★ Green Device Available
★ Super Low Gate Charge
★ Excellent CdV/dt effect decline
★ Advanced high cell density Trench technology

Product Summary

Green

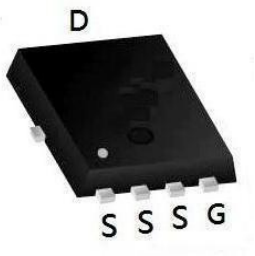
BVDSS	RDSON	ID
40V	13.4mΩ	20A

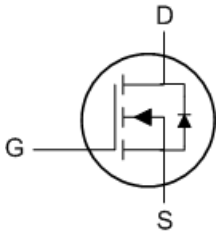
Description

The XR20N04D is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

The XR20N04D meet the RoHS and Green Product requirement with full function reliability approved.

PDFN3333-8L Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	20	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	12	A
I_{DM}	Pulsed Drain Current[2]	80	A
EAS	Single Pulse Avalanche Energy[3]	28	mJ
I_{AS}	Avalanche Current	20	A
P_D@T_C=25℃	Total Power Dissipation[4]	12.5	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	10	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	40	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	---	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=5A	---	13.4	18	mΩ
		V_{GS}=4.5V , I_D=4A	---	14.9	20	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1	1.2	2	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=40V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=40V, V_{GS}=0V , T_J=100℃	---	---	100	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
Q_g	Total Gate Charge	V_{DS}=20V , V_{GS}=10V , I_D=5A	---	12	---	nC
Q_{gs}	Gate-Source Charge		---	2	---	
Q_{gd}	Gate-Drain Charge		---	2.5	---	
$T_{d(on)}$	Turn-On Delay Time	V_{GS}=10V, V_{DD}=20V, ID=5A， R_{GEN}=3Ω	---	10	---	ns
T_r	Rise Time		---	12	---	
$T_{d(off)}$	Turn-Off Delay Time		---	33	---	
T_f	Fall Time		---	9	---	
C_{iss}	Input Capacitance	V_{DS}=20V , V_{GS}=0V , f=1MHz	---	850	---	pF
C_{oss}	Output Capacitance		---	78	---	
C_{rss}	Reverse Transfer Capacitance		---	69	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	20	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=7.5A , T_J=25C	---	---	1.2	V
t_{rr}	Reverse Recovery Time	IF=3A , di/dt=100A/ μs , T_J= 2 5 C	---	---	---	nS
Q_{rr}	Reverse Recovery Charge		---	---	---	nC

Note :

1. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 0.5%
2. The EAS data shows Max. rating . The test condition is V_{DD}=20V,V_{GS}=10V,R_G=250ohm,L=0.5mH,I_{AS}=20A
3. The power dissipation is limited by 150℃ junction temperature

Typical Performance Characteristics-N

Figure1: Output Characteristics

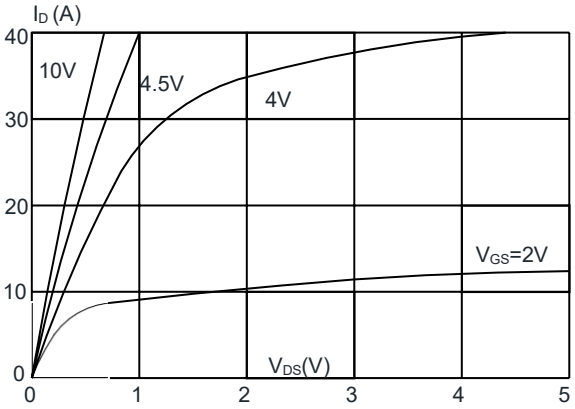


Figure 2: Typical Transfer Characteristics

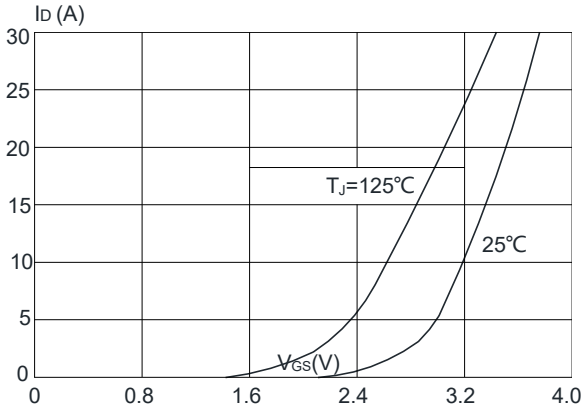


Figure 3: On-resistance vs. Drain Current

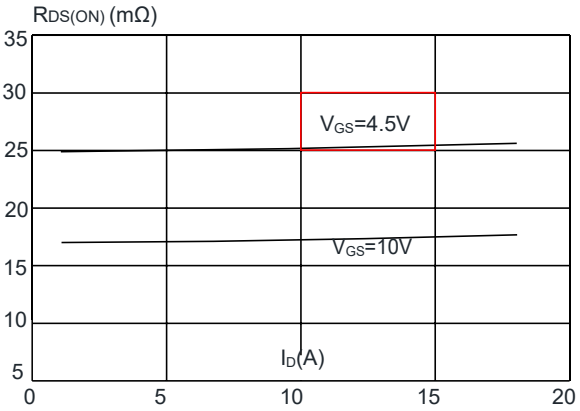


Figure 4: Body Diode Characteristics

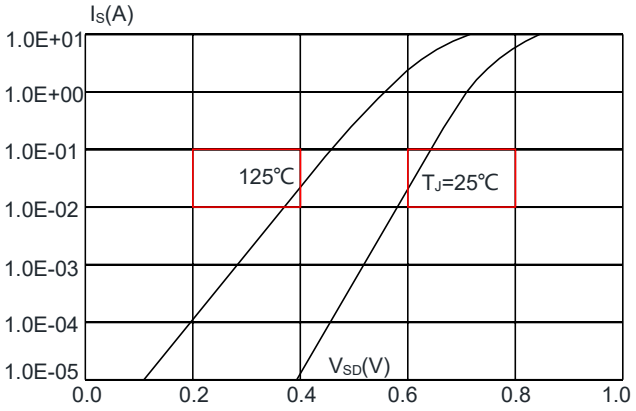


Figure 5: Gate Charge Characteristics

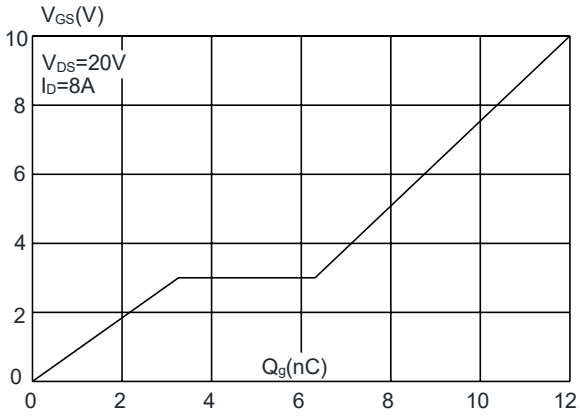


Figure 6: Capacitance Characteristics

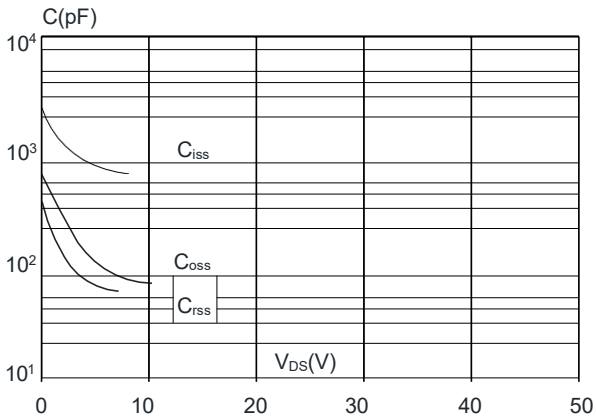


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

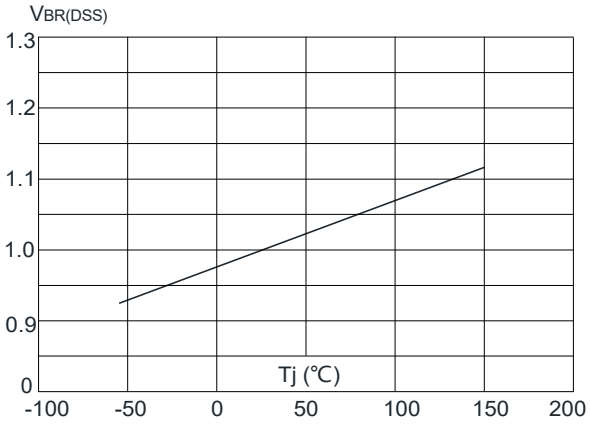


Figure 8: Normalized on Resistance vs. Junction Temperature

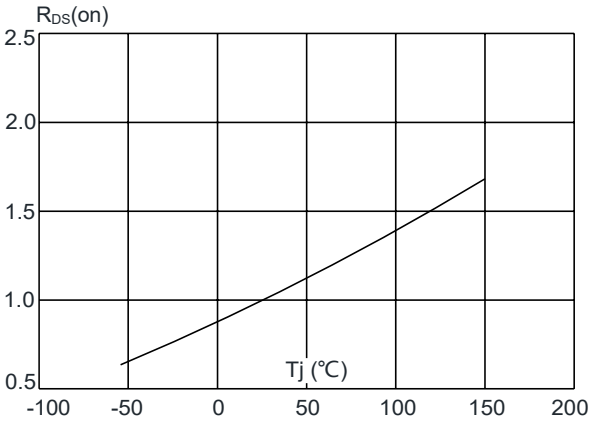


Figure 9: Maximum Safe Operating Area

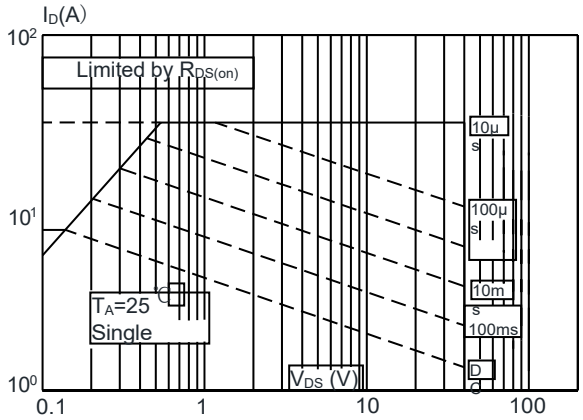


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

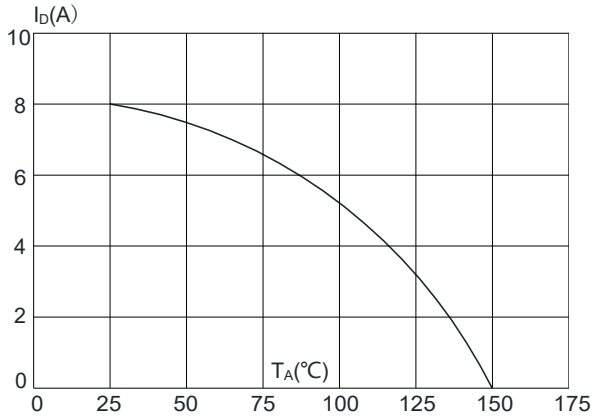
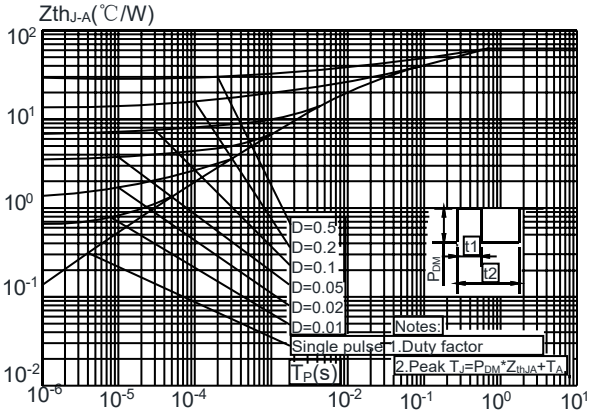
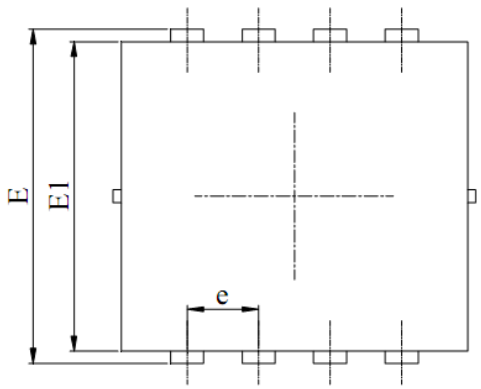


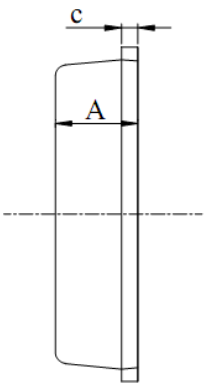
Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



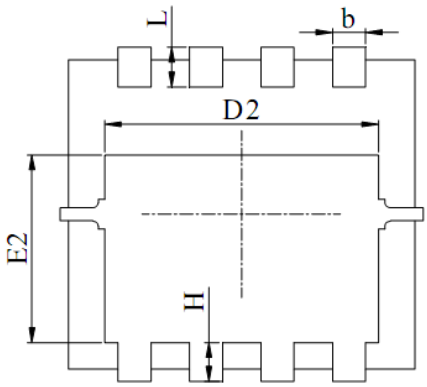
Package Mechanical Data-PDFN3333-8L-Single



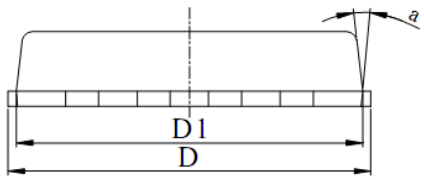
Top View



Side View



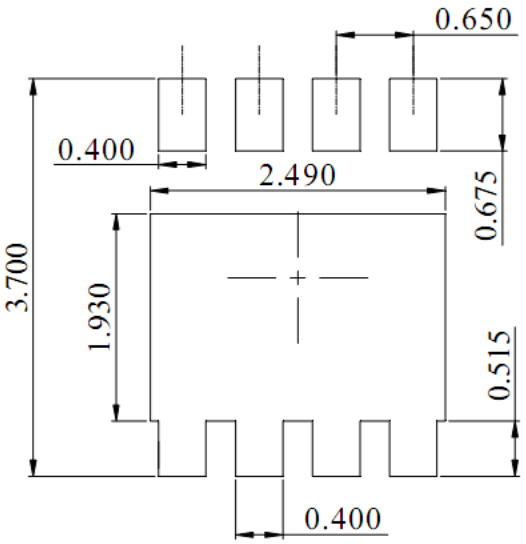
Bottom View



Front View

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. ALL DIMNESIONS IN MILLIMETER (ANNGLE IN DEGREE).
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.20	0.25
D	3.00	3.15	3.25
D1	2.95	3.05	3.15
D2	2.39	2.49	2.59
E	3.20	3.30	3.40
E1	2.95	3.05	3.15
E2	1.70	1.80	1.90
e	0.65 BSC		
H	0.30	0.40	0.50
L	0.25	0.40	0.50
a	---	---	15°



DIMENSIONS:MILLIMETERS